

N-Channel Power MOSFET

600V, 4.0A, 2.5Ω

FEATURES

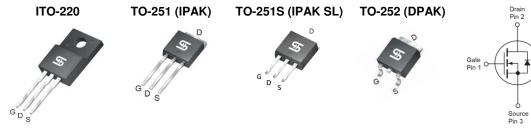
- 100% Avalanche Tested
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

KEY PERFORMANCE PARAMETERS				
PARAMETER	R VALUE UNIT			
V_{DS}	600	V		
R _{DS(on)} (max)	2.5	Ω		
Q_g	14.5	nC		

APPLICATION

- Power Supply
- Lighting





Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (D-PAK) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER	SYMBOL	IPAK/DPAK	ITO-220	UNIT	
Drain-Source Voltage	V_{DS}	600		V	
Gate-Source Voltage	V_{GS}	±30		V	
Continuous Drain Current (Note 1) $T_C = 25^{\circ}C$		4.0			
T _C = 100°C	l _D	2.4	ļ	Α	
Pulsed Drain Current (Note 2)	I _{DM}	16		Α	
Total Power Dissipation @ $T_C = 25$ °C	P _{DTOT}	50	25	W	
Single Pulsed Avalanche Energy (Note 3)	E _{AS}	70		mJ	
Single Pulsed Avalanche Current (Note 3)	I _{AS}	4		Α	
Repetitive Avalanche Energy (Note 2)	E _{AR}	5		mJ	
Peak Diode Recovery (Note 4)	dV/dt	4.5)	V/ns	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	- 55 to +150		°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	IPAK/DPAK	ITO-220	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	2.5	5	°C/W	
Junction to Ambient Thermal Resistance	R _{eJA}	83	62.5	°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JC}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.

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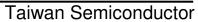


ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 5)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	$V_{GS(TH)}$	2.5	3.5	4.5	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I _{DSS}			1	μΑ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.0A$	R _{DS(on)}		2.2	2.5	Ω
Forward Transfer Conductance	$V_{DS} = 40V, I_{D} = 2A$	g _{fs}		2.6		S
Dynamic (Note 6)						
Total Gate Charge	$V_{DS} = 480V, I_D = 4.0A,$	Q_g		14.5		
Gate-Source Charge		Q_{gs}		3.4		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q_gd		7		1
Input Capacitance), of),),	C _{iss}		500		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		53.2		pF
Reverse Transfer Capacitance	1 = 1.0WITZ	C_{rss}		7		
Switching (Note 7)						
Turn-On Delay Time	$V_{DD} = 300V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 4.0A, V_{GS} = 10V,$	t _{d(on)}		11		
Turn-On Rise Time		t _r		20		
Turn-Off Delay Time		t _{d(off)}		30		ns
Turn-Off Fall Time	1D = 4.0A, VGS = 10V,	t _f		19		
Source-Drain Diode (Note 5)						
Forward On Voltage	$I_{S} = 4.0A, V_{GS} = 0V$	V_{SD}			1.13	V
Reverse Recovery Time	$V_{GS} = 0V, I_S = 2A$	t _{rr}		522		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		1.6		μC
Source Current	Integral reverse diode	I _S			4	Α
Source Current (Pulse)	in the MOSFET	I _{SM}			16	Α

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Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. L=8mH, $I_{AS}=4.0A$, $V_{DD}=50V$, $R_G=25\Omega$, Starting $T_J=25^{\circ}C$. 100% Eas Test Condition: L=8mH, $I_{AS}=2A$, $V_{DD}=50V$, $R_G=25\Omega$, Starting $T_J=25^{\circ}C$
- 4. $I_{SD} \le 4A$, $dI/dt \le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25$ °C.
- 5. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%.
- 6. For DESIGN AID ONLY, not subject to production testing.
- 7. Switching time is essentially independent of operating temperature.





ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM4NB60CI C0G	ITO-220	50pcs / Tube
TSM4NB60CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM4NB60CH X0G	TO-251S (IPAK SL)	75pcs / Tube
TSM4NB60CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Version: L1901

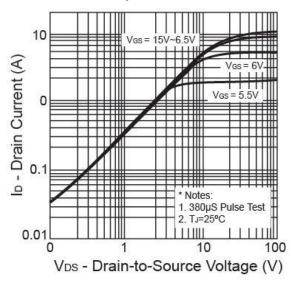
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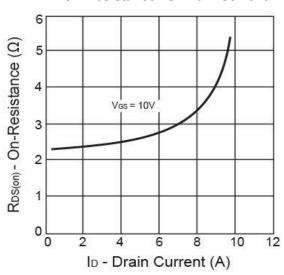
CHARACTERISTICS CURVES

(T_C = 25°C unless otherwise noted)

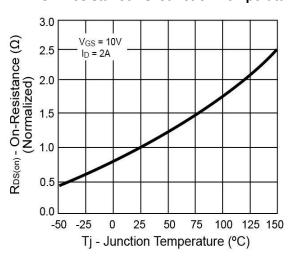
Output Characteristics



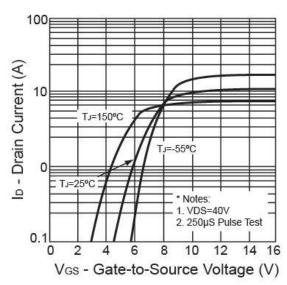
On-Resistance vs. Drain Current



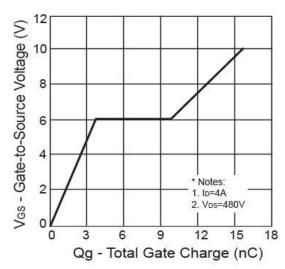
On-Resistance vs. Junction Temperature



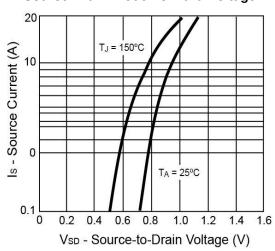
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



Version: L1901

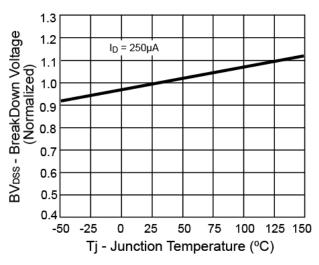
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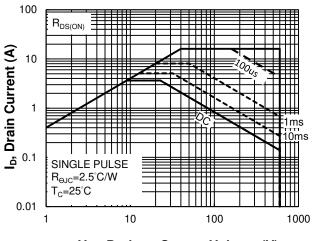
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

Breakdown Voltage vs. Temperature

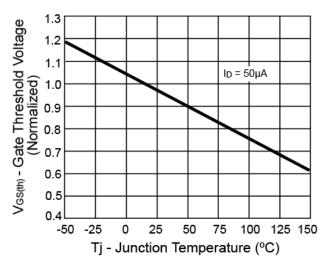


Maximum Safe Operating Area (IPAK/DPAK)

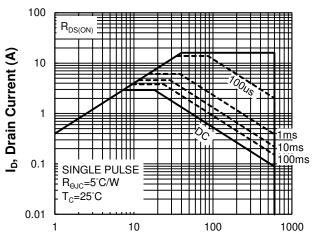


V_{DS}, Drain to Source Voltage (V)

Threshold Voltage vs. Temperature



Maximum Safe Operating Area (ITO-220)



V_{DS}, Drain to Source Voltage (V)

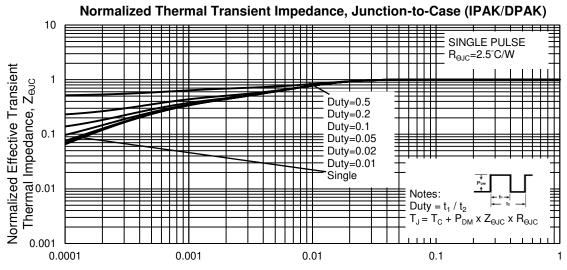
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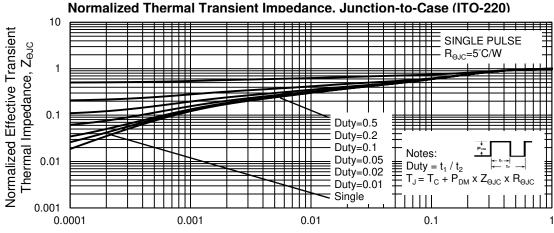


ELECTRICAL CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



t, Square Wave Pulse Duration (sec)

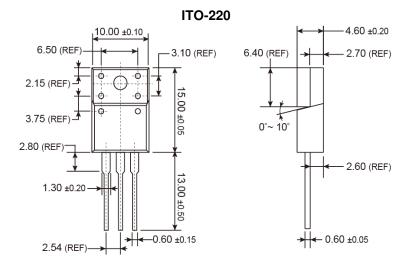


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t, Square Wave Pulse Duration (sec)

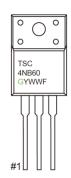






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MARKING DIAGRAM



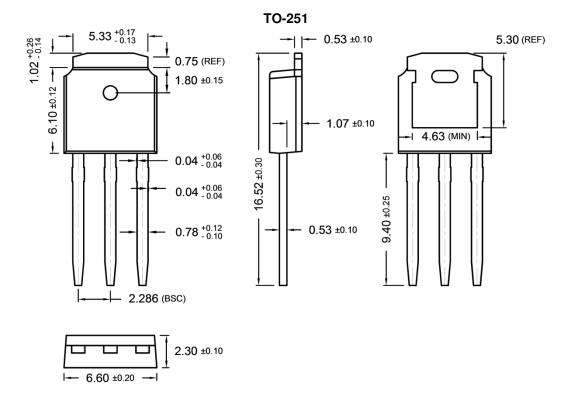
G = Halogen Free

Y = Year Code

WW = Week Code (01~52)

F = Factory Code





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MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

P =Feb O =Jan **Q** =Mar R =Apr

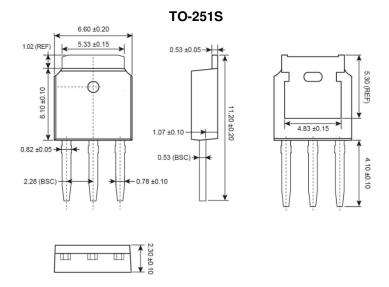
S =May T =Jun V =Aug **U** =Jul

W =Sep X =Oct Y =Nov **Z** =Dec

L = Lot Code (1~9, A~Z)







MARKING DIAGRAM



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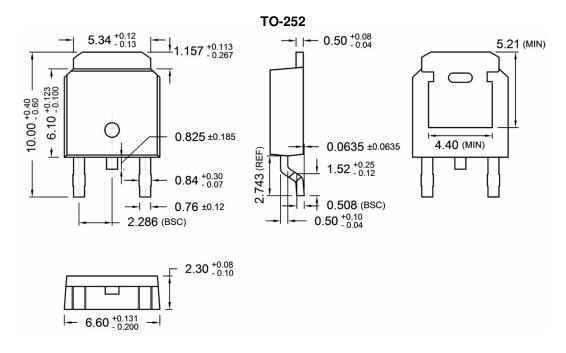
S =May **T** =Jun V =Aug

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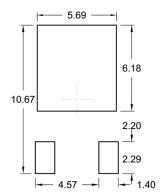
U =Jul **Z** =Dec Y =Nov

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SUGGESTED PAD LAYOUT (Unit: Millimeters)



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